



NEW DETECTING CELLS FOR «SHASLIK» TYPE calorimeter based on GaGG crystals.

REQUIREMENTS FOR **SPD** CALORIMETER

-TO MINIMIZE THE MOLIERE RADIUS < **15mm** and CELL LENGTH

if **X₀ < 5mm** → size of detecting cell (**20 X₀**) **~ 15x15x 100 mm³ !!!**

- FAST RESPONSE

< 50 ns

- TO USE RADIATION-HARD MATERIALS

> 100 MRAD

- TO USE WLS or TRANSPORT CAPILLARIES FOR WAVELENTGH SHIFTING
to data collection boxes

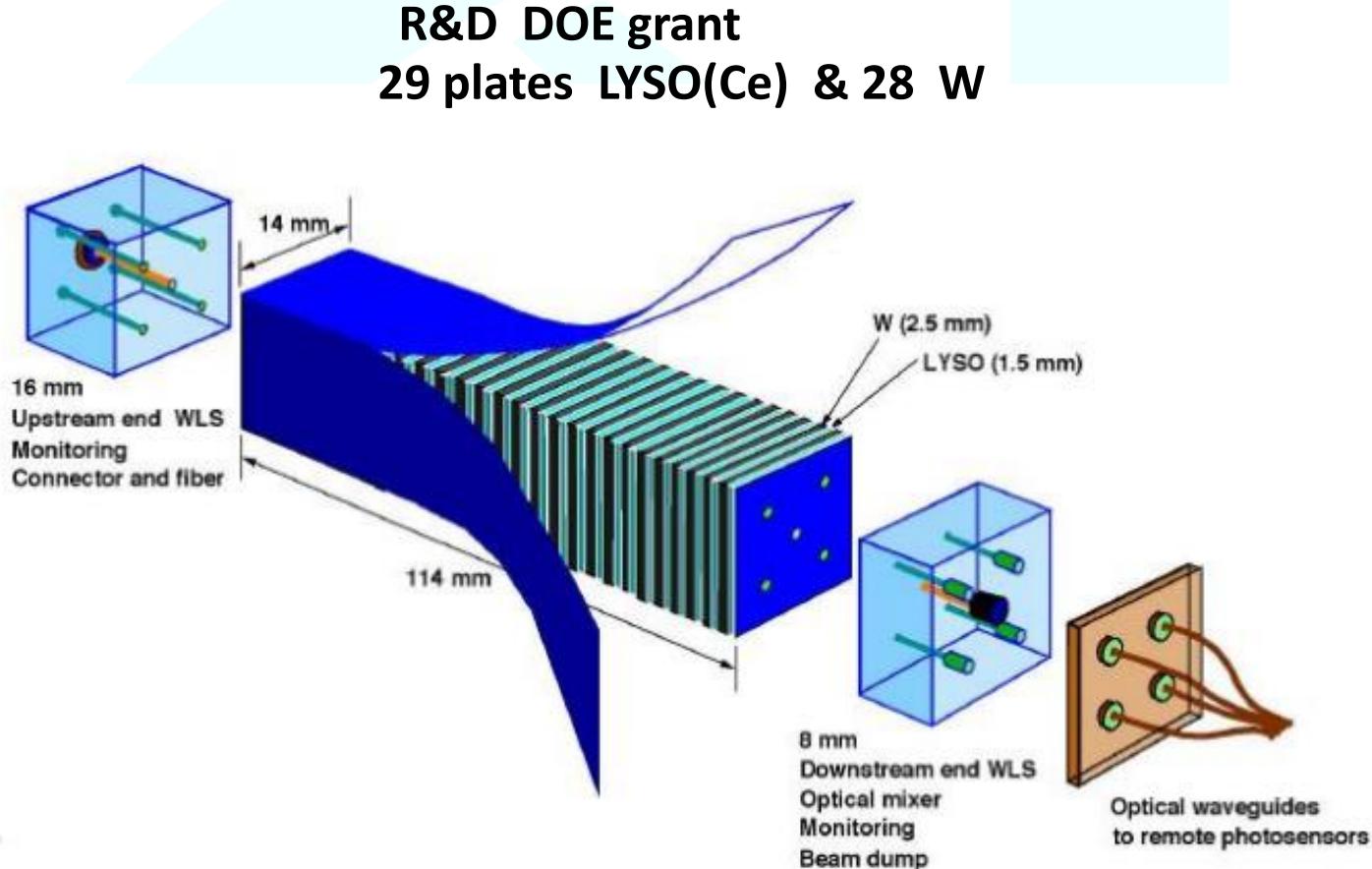
Suggested solution

Shashlik configuration

based upon interleaved W and GaGG crystals plates

TOTALLY (50 -60) PIECES PER CELL

Test setup W- LYSO(Ce) cell for upgrade CMS calorimeter



SPD prototype
29 plates **GaGG(Ce)**
 $\text{Gd}_3\text{Al}_2\text{Ga}_3\text{O}_{12}$
20X 20X2 mm³
& **28 W** powder plates
20x20 x2 mm³
all plates **2 mm**

**Table 1. Comparison of LYSO/W Shashlik Module
with conventional Lead Tungstate Crystal**

	W/LYSO:Ce Module	PbWO ₄ Crystal
Length (mm)	114	220
Transverse size (mm)	14	28.6
Average Molière Radius (mm)	13.7	21
Average Radiation Length X ₀ (mm)	5.1	8.9
Crystal Light Yield (relative to NaI = 100)	85	0.3
Emission Wavelength	425	425
Decay time (ns)	40	25
Light Output (p.e./MeV)	6-8	2
Temp Dependence (%/C)	-0.2	-2.2

Optical electromagnetic calorimetry for high
energy experimental app.... (draft)

Why GaGG

Material	LY, Ph/MeV	dE/dx @ e ⁻ , MeV/mm	Yield, ph per 1 mm per MIP	Radiation hardness to protons
Plastic scintillator (vinyltoluene based)	10 000	0.154	1 540	-
Y ₃ Al ₅ O ₁₂ (YAG)	11 000	0.591	6 500	+
(Lu-Y)AlO ₃	30 000	0.614	18 420	-
YAlO ₃ (YAP)	16 000	0.708	11 350	-
Gd ₃ Al ₂ Ga ₃ O ₁₂ (GAGG)	46 000	0.808	37 200	+
Lu ₂ SiO ₅ (LSO)	27 000	0.879	23 700	+
(Lu _{0.8} -Y _{0.2}) ₂ SiO ₅ (LYSO)	30 000	0.85	25 500	+

In general:

GAGG shows the best yield per MIP- 37200 Ph/mm,

RADHARD & ROBUST similar to diamond ,

Energy resolution ~ 4 % on 662 keV with SiPM

Energy deposit per MIP for different crystal

Ionization losses per 1 mm of the media for 10GeV e⁻ and 50Gev π⁻

Material	Density ρ, g/cm ³	dE/dx @ e ⁻ , MeV/mm	dE/dx @ π ⁻ , MeV/mm
Plastic scintillator (vinyltoluene based)	1.032	0.154	0.154
Y ₃ Al ₅ O ₁₂ (YAG)	4.55	0.591	0.589
Y ₃ (Al _{0.5} -Ga _{0.5}) ₅ O ₁₂	4.80	0.614	0.612
YAlO ₃ (YAP)	5.50	0.708	0.705
Gd ₃ Al ₂ Ga ₃ O ₁₂ (GAGG)	6.63	0.808	0.804
Lu ₂ SiO ₅ (LSO)	7.4	0.879	0.873
(Lu _{0.8} -Y _{0.2}) ₂ SiO ₅ (LYSO)	7.2	0.85	0.85

Light output per MIP (10GeV e⁻) per 1 mm in different scintillation materials

Material	LY, Ph/MeV	dE/dx @ e ⁻ , MeV/mm	Yield, ph per 1 mm per MIP
Plastic scintillator (vinyltoluene based)	10 000	0.154	1 540
Y ₃ Al ₅ O ₁₂ (YAG)	11 000	0.591	6 500
Y ₃ (Al _{0.5} -Ga _{0.5}) ₅ O ₁₂	30 000	0.614	18 420
YAlO ₃ (YAP)	16 000	0.708	11 350
Gd ₃ Al ₂ Ga ₃ O ₁₂ (GAGG)	46 000	0.808	37 200
Lu ₂ SiO ₅ (LSO)	27 000	0.879	23 700
(Lu _{0.8} -Y _{0.2}) ₂ SiO ₅ (LYSO)	30 000	0.85	25 500

Already Grown GGAG Crystals

Up to now JSC Fomos-Materials grew GGAG crystals with following compositions:

- GGAG:Ce with different cerium concentrations
- GGAG:Ce with different Ga/Al ratio
- GGAG:Ce with codoping of:



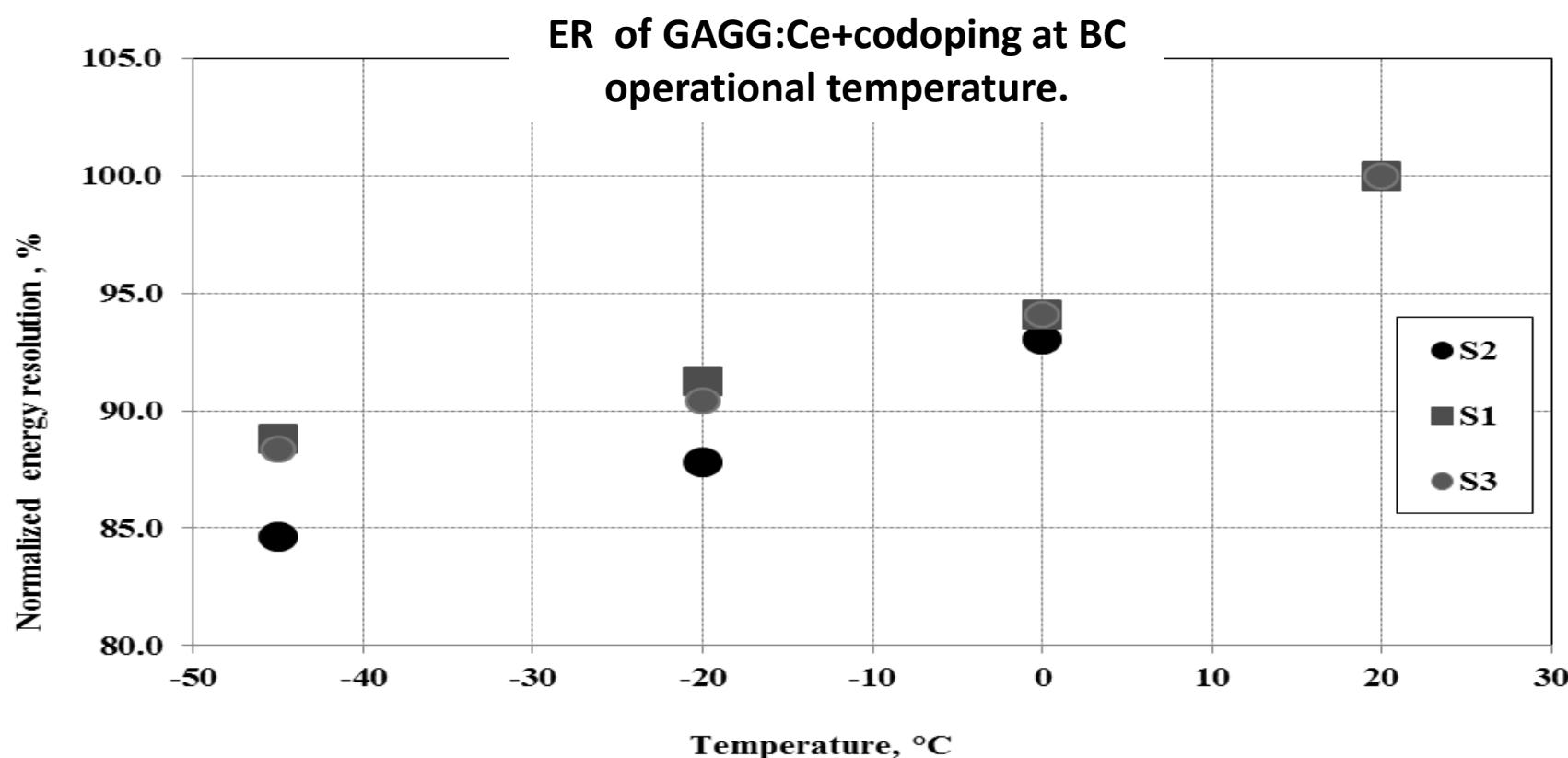
Magnesium
Calcium
Strontium
Barium
Scandium
Zirconium
Titanium

- GGAG:Ce with pair and triple codoping of above listed elements



*A favorable decision of
the Federal Service for Intellectual
Property (Rospatent) concerning the
issuance of the patent has been received.
Application 2017119423/05(033718)*

Modern trend : to operate at temperature below 0°C to reduce noise while operating with SiPM

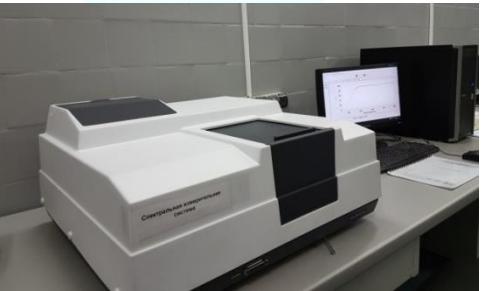


Temperature change of energy resolution FWHM at 662 keV normalized to result room temperature. Measurements have been performed with 1000 ns time gate.

**Radiation Instruments and
New Components LLC**

Full Technological Circle

- ▶ ***Initial Charge Synthesis***
- ▶ ***Crystal Growing***
- ▶ ***High Temperature Heat Treatment***
- ▶ ***Cutting, Grinding, Drilling, Polishing.***





**THANK YOU FOR YOUR
ATTENTION**